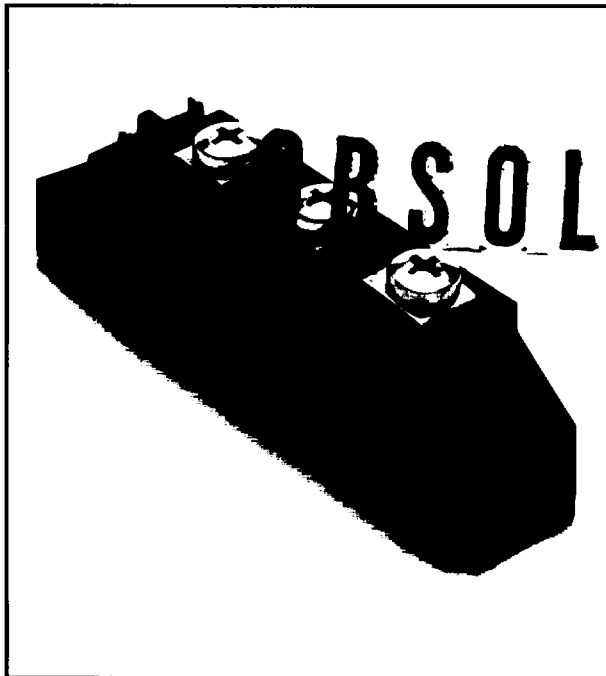


SCR Diode Module (110 Amp)



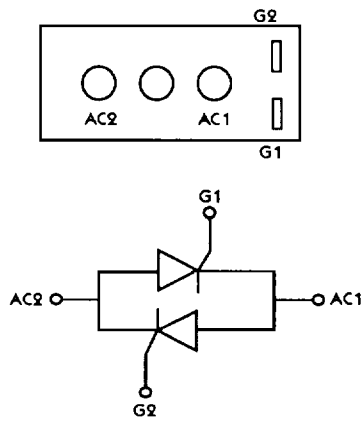
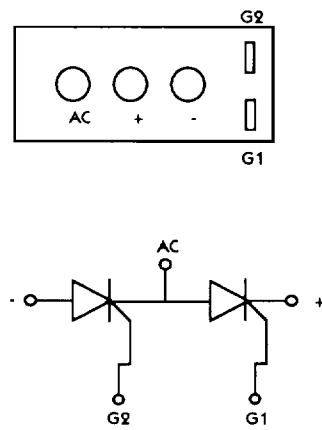
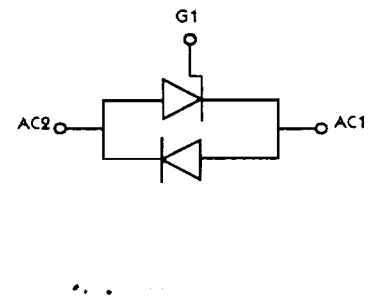
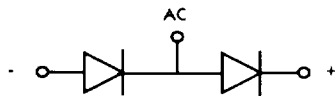
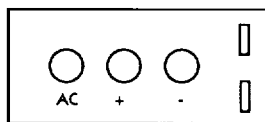
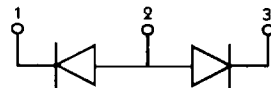
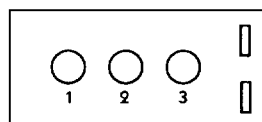
Outline/Mounting Dimensions

DIMENSION	INCHES	
	MINIMUM	MAXIMUM
A	3.630	3.610
B	0.797	0.777
D	0.797	0.777
E	0.520	0.480
F	1.205	1.160
G	1.100	1.070
H	3.155	3.145
J	0.130	0.120
K	0.250	0.240
L	0.380	0.370
M	0.249	0.239

MOUNTING TORQUE REQUIRED:

(A) Mounting Screws 20 in. lbs.
 (B) Terminal Studs 30 in. lbs.

PARAMETERS	SYM.	UNITS	SPECIFICATION LIMITS	CONDITIONS
Average Output Current per Device	I_o	A	110	$T_c = 85^\circ \text{C}$
One-Cycle Surge Current (Peak)	I_{TSM}	A	1,600	$T_c = 125^\circ \text{C}$ Non-Repetitive
I^2t for Fusing (Max.)	I^2T	A^2S	12,750	$T_c = 125^\circ \text{C}$ Non-Repetitive
Rate-of-Rise On-State Current (Max.)	di/dt	$\text{A}/\mu\text{S}$	150	Max. V_{DM} Peak On-State Current = $9 \times I_o$ (Max.)
Rate-of-Rise Off-State Voltage (Max.)	dv/dt	$\text{A}/\mu\text{S}$	500	Exponential Rise to 80% V_{DM} Gate Open Circuit $T_c = 125^\circ \text{C}$
Reverse Blocking Voltage (Max.)	V_{DRM}	V	1,200	$T = 125^\circ \text{C}$
Leakage Current (Max.)	I_{RM}	mA	30	$T = 125^\circ \text{C}$ at Rated Voltage
Isolation Voltage (Min.)	V_{ISOL}	V _{RMS}	2500V	Any Terminal-to-Base
Junction Operating and Storage Temperature Range	T_j & T_{SVG}	$^\circ \text{C}$	-40 to 125	
Thermal Resistance (Case-to-Sink)	R_{j-c}^*	$^\circ \text{C}/\text{W}$	0.1	With Thermal Grease
Thermal Resistance (Junction-to-Case)	R_{j-c}^*	$^\circ \text{C}/\text{W}$	0.18	per Module
Forward Gate Current (Peak)	I_{FORM}	A	3.0	
Gate Current Required to Fire All Devices (Max.)	I_{GT}	mA	120	D mode Supply = CV Resistive Load
Reverse Gate Voltage (Peak)	V_{RGM}	V	2.0	
Gate Voltage Required to Fire (Max.)	V_{GT}	V	2.5	N mode Supply = CV Resistive Load
Holding Current (Max.)	I_w	mA	200	$T_j = 25^\circ \text{C}$ $V_A = 12\text{V}$
Gate Power (Peak)	P_{GM}	W	12	$T_p = 5 \text{ ms}$

SCR 110D-1**SCR 110D-2****SCR 110D-3****D 110D-1****D 110D-2****D 110D-3**